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**Itoh**

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[54] **CURRENT SOURCE CIRCUIT**

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[52] **U.S. Cl.** ..... **327/530; 323/312; 323/315**

[58] **Field of Search** ..... **323/312, 313, 323/315; 327/530, 560, 575, 577, 403, 405, 538, 543**

[56] **References Cited**

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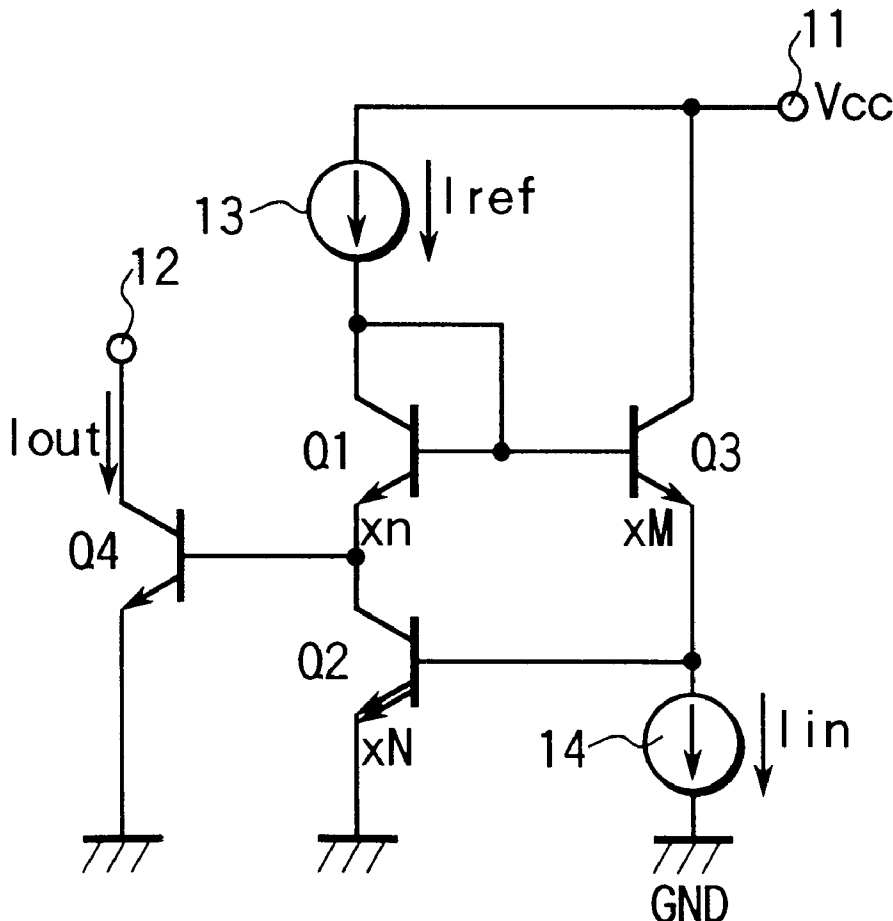
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[57] **ABSTRACT**

A current source circuit includes a series-circuit connected between a power source node and ground and comprising a reference current source circuit, a first transistor Q1 of an NPN type having its collector and base connected to each other and a second transistor Q2 having a multi-emitter area (N) and having a multi-emitter configuration. The current source circuit further includes a third transistor Q3 of an NPN type connected at its collector to the power source node, at its base to the base of the first transistor Q1 and at its emitter connected to the base of the second transistor and has an emitter area (M) and an input current source circuit connected between the emitter of the third transistor Q3 and ground to allow a flow of an input current I<sub>in</sub>. The current source circuit still further includes a fourth transistor Q4 of an NPN type connected at its collector-to-emitter circuit between a current output node and the ground and at its base connected to the collector of the second transistor to allow a flow of an output current I<sub>out</sub>. Relative to an input current I<sub>in</sub>, the output current I<sub>out</sub> is proportional to the reciprocal of a product (M×N) of emitter areas of the third transistor Q3 and second transistor Q2.

8 Claims, 4 Drawing Sheets



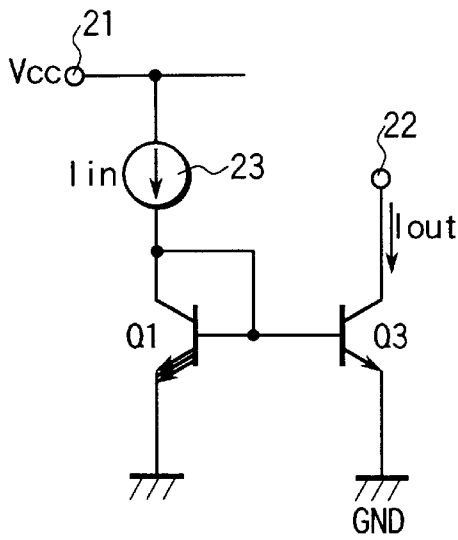


FIG. 1  
PRIOR ART

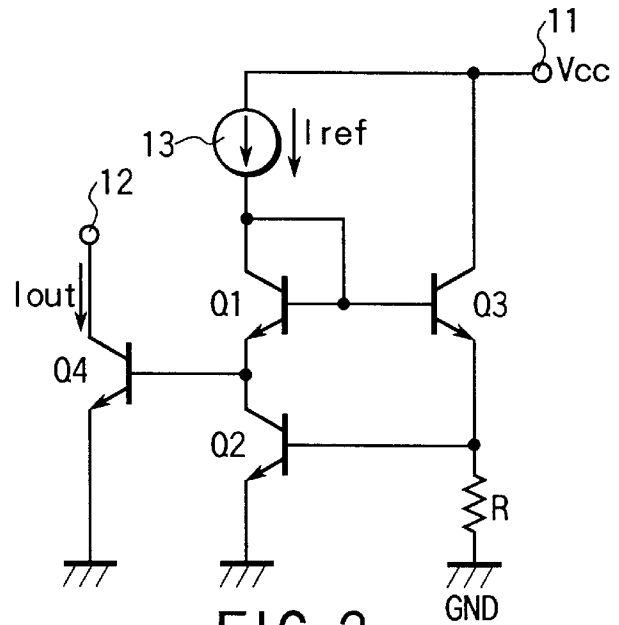


FIG. 2  
PRIOR ART

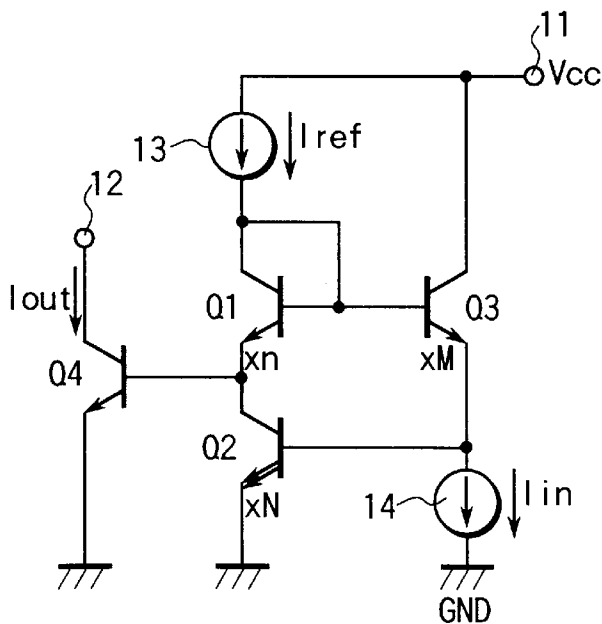


FIG. 3



FIG. 7

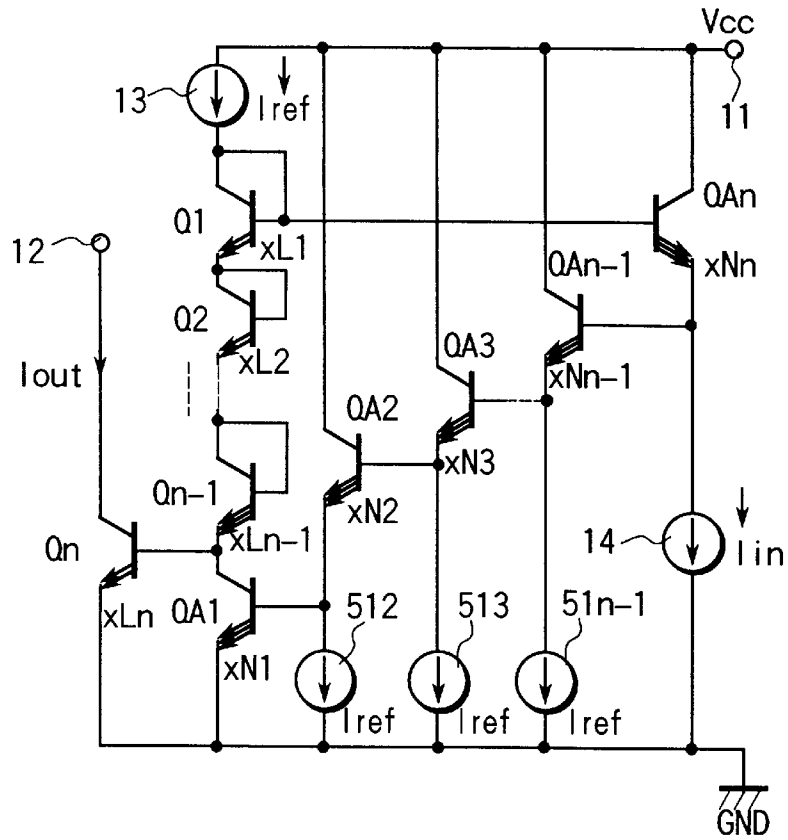
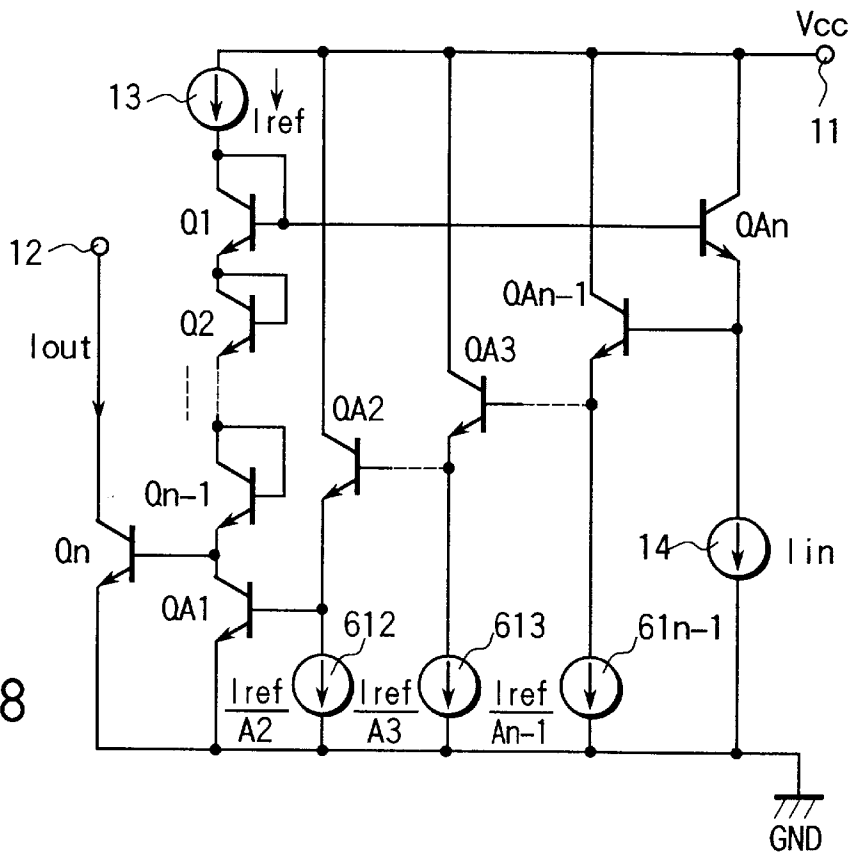


FIG. 8



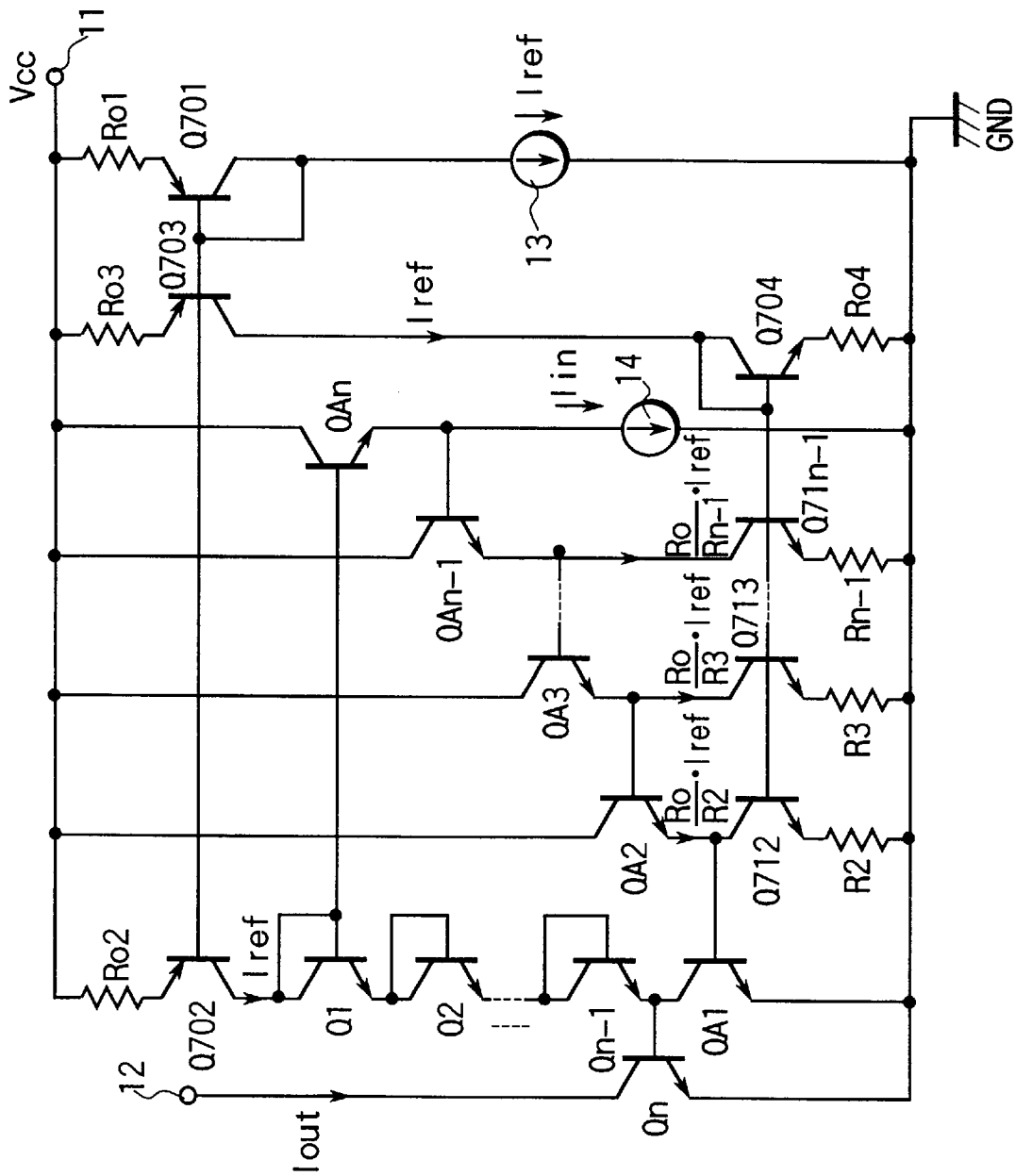


FIG. 9

## CURRENT SOURCE CIRCUIT

## BACKGROUND OF THE INVENTION

The present invention relates to a current source circuit formed in a semiconductor integrated circuit (IC) and, in particular, to a bipolar type very small current source circuit, demanding an output current of high accuracy, which is used as a current source of an electronic circuit for application to an automobile, home electric appliance, industrial machine and equipment.

A conventional bipolar type very small current source circuit as shown in FIG. 1 is represented by a power source node **21** supplied with a current source voltage  $V_{cc}$ , a current output node **22** (a current drawing node in this example) to which a load circuit is connected, and ground GND, in which an input current source circuit **23** and first NPN transistor **Q1** of a multi-emitter configuration are connected, in a series array, between the current source node **21** and the GND, the input current source circuit **23** supplying an input current  $I_{in}$  and the first NPN transistor **Q1** having its collector and base connected to each other, its collector connected to an output of the input current source circuit **23** and its multi-emitter side connected to the GND.

Further, a collector-to-emitter circuit of a second NPN transistor **Q3** is connected between the current output node **22** and the GND and has its base connected to the base of the transistor **Q1**.

In the current source circuit above, the collector current in the transistor **Q1** is substantially  $I_{in}$  and if, in this case, those emitter areas  $A_1$  and  $A_2$  of these transistors **Q1** and **Q3** are given as a ratio of  $K$  (integer):1, then an output current  $I_{out}$  flowing through the transistor **Q3** and output node **22** is given as

$$I_{out} = I_{in}/K.$$

It is necessary that, in order to obtain a very small output current  $I_{out}$  in a current attenuation circuit for instance, the emitter area ratio  $K:1$  be made greater. In order to set  $K=25$  for instance, the pattern size of the transistor **Q1** becomes considerably greater (size corresponding to 25 transistors) and, correspondingly, the size of the IC chip becomes considerably greater.

A very small current source circuit of FIG. 2 constituting another prior art circuit is represented by a power supply node **11** supplied with a power source voltage  $V_{cc}$ , current output node **12** (current drawing node in this example) connected to a load circuit, and ground GND. Between the power source node **11** and the GND is connected a series circuit of a reference current source circuit **13** supplied with a reference current  $I_{ref}$ , a collector-to-emitter circuit of a first NPN transistor **Q1** having its collector and base connected to each other, and a collector-to-emitter circuit of a second NPN transistor **Q2**.

Further a collector-to-emitter circuit of a third NPN transistor **Q3** and resistive element  $R$  are connected, in a series array, between the power source node **11** and the GND.

The base of the transistor **Q1** is connected to that of the transistor **Q3** and the base of the transistor **Q2** is connected to the emitter of the transistor **Q3**.

Further, a collector-to-emitter circuit of a fourth NPN transistor **Q4** is connected between the current output node **12** and the GND. The base of the transistor **Q4** is connected to the collector of the transistor **Q2**.

In the current source circuit above, the base-to-emitter forward voltage of the transistor **Q1** is represented by

$V_{BEQ1}$ , base-to-emitter forward voltage of the transistor **Q2** by  $V_{BEQ2}$ , base-to-emitter forward voltage of the transistor **Q3** by  $V_{BEQ3}$  and base-to-emitter forward voltage of the transistor **Q4** by  $V_{BEQ4}$  and collector current (output current) of the transistor **Q4** by  $I_{out}$ , then a potential  $V_x$  on the base of the transistor **Q4 is given by:**

$$\begin{aligned} V_x &= V_{BEQ2} + V_{BEQ3} - V_{BEQ1} \\ &= VT \cdot \ln\{I_{ref}/(\beta \cdot I_s)\} + VT \cdot \ln\{V_{BEQ2}/(R \cdot \beta \cdot I_s)\} - VT \cdot \ln\{I_{ref}/(\beta \cdot I_s)\} \\ &= VT \cdot \ln\{I_{ref}/(\beta \cdot I_s)\} * \{V_{BEQ2}/(R \cdot \beta \cdot I_s)\} * \{\beta \cdot I_s/I_{ref}\} \\ &= VT \cdot \ln\{V_{BEQ2}/(R \cdot \beta \cdot I_s)\} \\ &= VT \cdot \ln\{I_{out}/(\beta \cdot I_s)\} \end{aligned} \quad (1)$$

Here,  $VT$ : thermal voltage

$\beta$ : current amplification factor

$I_s$ : saturation current

From the equation (1) the following equation (2) is found:

$$I_{out} = V_{BEQ2}/R \quad (2)$$

That is, the output current  $I_{out}$  is proportional to the reciprocal ( $1/R$ ) of the resistive value of the resistive element  $R$ . In order to obtain a very small output current  $I_{out}$ , it is only necessary to make the resistive value of the resistive element  $R$  greater. In this case, however, the pattern size of the resistive element  $R$  is made considerably greater and hence the size of the IC chip becomes considerably bulkier.

The conventional current source circuit above has the drawback in that, in order to obtain a very small output current, the pattern size of those elements used becomes considerably greater and hence the size of the IC chip becomes considerably greater.

## BRIEF SUMMARY OF THE INVENTION

It is accordingly the object of the present invention to provide a current source circuit which is simpler in construction and can precisely obtain a very small output current while suppressing the size of an integrated circuit as well as the pattern size of elements used.

In order to achieve the above-mentioned object, there is provided a current source circuit comprising:

a series-circuit connected between a power source node and ground and comprised of a reference current source circuit, a first transistor **Q1** of NPN type having its collector and base connected to each other and a second transistor **Q2** of a multi-emitter configuration having an emitter area ( $N$ );

a third transistor **Q3** of an NPN type connected at its collector connected to the power source node, at its base connected to the base of the first transistor **Q1** and at its emitter to the base of the second transistor **Q2** and having an emitter area ( $M$ );

an input current source circuit connected between the emitter of the third transistor **Q3** and the ground to provide an input current  $I_{in}$ ; and

a fourth transistor **Q4** of an NPN type having its collector-to-emitter circuit connected between a current output node and the ground and its base connected to the collector of the second transistor **Q2** to provide an output current  $I_{out}$ , wherein, relative to an input current  $I_{in}$ , the output current  $I_{out}$  is proportional to a reciprocal of a product ( $M \times N$ ) of the emitter areas of the second and third transistors **Q2** and **Q3**.

Further, a current source circuit is provided, comprising:

- a first transistor Q1 of a PNP type having its emitter connected to a power source node and its collector and base connected to each other;
- a second transistor Q2 of an NPN type having its collector-to-emitter circuit connected between the collector of the first transistor Q1 and ground and being a multi-emitter configuration having an emitter area (N);
- a third transistor Q3 of a PNP type connected at its emitter to the power source node and at its base connected to the base of the first transistor Q1;
- a fourth transistor Q4 of an NPN type having its collector-to-emitter circuit connected between the collector of the third transistor Q3 and the ground and its collector and base connected to each other;
- a fifth transistor Q5 of an NPN type connected at its base connected to the base of the fourth transistor Q4, its emitter connected to the ground and its collector connected to the base of the second transistor Q2 and being a multi-emitter configuration having an emitter area (M);

an input current source circuit connected between the power source node and the collector of the fifth transistor Q5; and

a sixth transistor Q6 of an NPN type having its collector-to-emitter circuit between a current output node and the ground and its base connected to the collector of the fifth transistor and serving as a current output transistor; wherein

relative to an input current  $I_{in}$ , an output current  $I_{out}$  is proportional to the reciprocal of a product (M×N) of those emitter areas of the second and fifth transistors Q2 and Q5.

Further, a current source circuit is provided, comprising:

- a first group of n-1 transistors (Q1, Q2, . . . , Qn-1) of an NPN type having one end connected to an other end of a reference current source circuit having one end connected to a power source node, having their collector and base connected to each other, having their emitter area ratios  $L1 \dots Ln-1$  and each having a multi-emitter configuration, these transistors being series-connected together and each providing a diode connection;
- an output transistor Qn of a multi-emitter configuration having its collector-to-emitter circuit connected between a current output node and ground and its base connected to the emitter of the transistor Qn-1 at the other end of the first transistor group and having an emitter area ratio  $L_n$ , the output transistor Qn providing an output current  $I_{out}$ ;
- a second group of transistors (QA1, QA2, . . . , QAn) comprising a first transistor QA1 of an NPN type having its collector-to-emitter circuit connected between the emitter of the transistor Qn-1 at the other end of the first group of transistors and ground and having a multi-emitter configuration, an n-th transistor QAn of an NPN type having its collector connected to the power source node and its base connected to the base of one transistor of the first transistor group and having a multi-emitter configuration, and n-2 transistors of an NPN type having a multi-emitter configuration and Darlington-connected between the base of the first transistor QA1 and the emitter of the n-th transistor QAn, the second group of transistors (QA1, QA2, . . . , QAn) having their emitter area  $N1, N2, \dots, N_n$ , wherein the collector-to-emitter circuits of the

- second to (n-1)-st transistors (QA2, . . . , QAn-1) of the second transistor group are connected between the power source node and the ground;
- an input current source circuits connected between the emitter of the n-th transistor QAn and the ground to provide an input current  $I_{in}$ ; and
- n-2 bias current source circuits connected between the corresponding emitters of the second to the n-1 transistors (QA2, . . . , QAn-1) of the second transistors group and the ground, wherein, relative to the input current  $I_{in}$ , the output current  $I_{out}$  is proportional to a product ( $L1 \cdot L2, \dots, L_n$ ) of those emitter area ratios of those diode-connected n-1 transistors Q1 to Qn-1 and output transistor Qn and proportional to the reciprocal of a product ( $N1 \cdot N2, \dots, N_n$ ) of the emitter area ratios of the second transistor group (QA1, QA2, . . . , QAn) where n represents an integer over 2.

Still further, a current source circuit is provided, comprising:

- a reference current source circuit having one end connected to a power source node;
- a first group of n-1 transistors (Q1, Q2, . . . , Qn-1) of an NPN type having one end connected to the other end of the reference current source circuit, each having its collector and base connected to each other, and series-connected together as a diode connection each;
- an output transistor Qn connected between a current output node and ground and connected at its base connected to the emitter of the transistor Qn-1 at the other end of the first transistor group to provide an output current  $I_{out}$ ;
- a second group of transistors (QA1, QA2, . . . , QAn) comprising a first transistor QA1 of an NPN type having a collector-to-emitter circuit connected between the emitter of the transistor Qn-1 at the other end of the first transistor group and ground, an n-th transistor QAn of an NPN type connected at its collector to the power source node and at its base connected to the base of one transistor of the first transistor group, and n-2 transistors of an NPN type Darlington-connected between the base of the first transistor QA1 and the emitter of the n-th transistor QAn, wherein the collector-to-emitter circuits of the second to the (n-1)-st transistors (QA2, . . . , QAn-1) of the second transistor group are connected between the power source node and the ground;
- n-2 bias current source circuits connected between the corresponding emitters of the second to (n-1)-st transistors (QA2, . . . , QAn-1) of the second transistor group and the ground to provide those corresponding weighted currents ( $I_{ref}/A2, I_{ref}/A3, \dots, I_{ref}/An-1$  where  $A2, A3, \dots, An-1$  represent the weighted factors); and
- an input current source circuit connected between the emitter of the n-th transistor QAn and the ground to provide an input current  $I_{in}$ , wherein
- the output current  $I_{out}$  is proportional to the reciprocal of a product ( $A2 \cdot A3 \cdot \dots \cdot An-1$ ) of the weighted factors given to the n-2 bias current source circuits for allowing a flow of the corresponding weighted currents ( $I_{ref}/A2, I_{ref}/A3, \dots, I_{ref}/An-1$ ) relative to the input current  $I_{out}$ .

By doing so, the current source circuit of the present invention can be made simpler in arrangement and precisely obtain a very small output current while suppressing the pattern size of elements used as well as the size of an IC chip.

Additional objects and advantages of the invention will be set forth in the description which follows, and in part will be obvious from the description, or may be learned by practice of the invention. The objects and advantages of the invention may be realized and obtained by means of the instrumentalities and combinations particularly pointed out in the appended claims.

#### BRIEF DESCRIPTION OF THE SEVERAL VIEWS OF THE DRAWING

The accompanying drawings, which are incorporated in and constitute a part of the specification, illustrate presently preferred embodiments of the invention, and together with the general description given above and the detailed description of the preferred embodiments given below, serve to explain the principles of the invention.

FIG. 1 is a schematic view showing one example of a conventional current source circuit;

FIG. 2 is a schematic view showing another example of a conventional current source circuit;

FIG. 3 is a schematic view showing a current source circuit according to a first embodiment of the present invention;

FIG. 4 is a schematic view showing a current source circuit according to a second embodiment of the present invention;

FIG. 5 is a schematic view showing a current source circuit according to a third embodiment of the present embodiment;

FIG. 6 is a schematic view showing a current source circuit according to a fourth embodiment of the present embodiment;

FIG. 7 is a schematic view showing a current source circuit according to a fifth embodiment of the present invention;

FIG. 8 is a schematic view showing a current source circuit according to a sixth embodiment of the present embodiment; and

FIG. 9 is a schematic view showing a current source circuit according to a seventh embodiment of the present embodiment.

#### DETAILED DESCRIPTION OF THE INVENTION

The embodiments of the present invention will be explained below with respect to the accompanying drawing.

FIG. 3 shows an arrangement of a current source circuit according to a first embodiment of the present invention.

A current source circuit formed in an integrated circuit includes a power source node **11** supplied with a power source voltage  $V_{cc}$ , a current output node **12** (a current drawing node in this embodiment) connected to a load circuit, and a ground potential GND (hereinafter referred to simply as GND).

Between the power source node **11** and the GND is connected a series circuit of a reference current source circuit **13** supplied with a reference current  $I_{ref}$ , a collector-to-emitter circuit of a first NPN transistor **Q1** having its collector and base connected to each other and a collector-to-emitter circuit of a second NPN transistor **Q2** of a multi-emitter configuration.

Further, between the power source node **11** and the GND is connected a series circuit of a collector-to-emitter circuit of a third NPN transistor **Q3** of a multi-emitter configuration and an input current source circuit **14** for supplying an input current  $I_{in}$ .

The base of the transistor **Q1** is connected to that of the transistor **Q3** and the base of the transistor **Q2** is connected to the emitter of the transistor **Q3**.

Further, the collector-to-emitter circuit of a fourth NPN transistor **Q4** is connected between the current output node **12** and the GND and the base of the transistor **Q4** is connected to the collector of the transistor **Q2**.

In the case where, in the current source circuit above, the emitter area of the transistor **Q4** is set as a reference (=1), the emitter area of the transistor **Q1** is set to n-fold, the emitter area of the transistor **Q2** N-fold and the emitter area of the transistor **Q3** M-fold.

If the base-to-emitter forward voltage of the transistor **Q1** is represented by  $V_{BEQ1}$ , base-to-emitter forward voltage of the transistor **Q2** by  $V_{BEQ2}$ , base-to-emitter forward voltage of the transistor **Q3** by  $V_{BEQ3}$ , base-to-emitter forward voltage of the transistor **Q4**, by  $V_{BEQ4}$ , and collector current (output current) of the transistor **Q4** by  $I_{out}$ , the base potential  $V_{BEQ4}$  of the transistor **Q4** is given by:

$$\begin{aligned} V_{BEQ4} &= V_{BEQ2} + V_{BEQ3} - V_{BEQ1} \\ &= VT \cdot \ln\{I_{ref}/(N \cdot \beta \cdot I_s)\} + VT \cdot \ln\{I_{in}/(M \cdot \beta \cdot I_s)\} - VT \cdot \ln\{I_{ref}/(n \cdot \beta \cdot I_s)\} \\ &= VT \cdot \ln\{I_{ref}/(N \cdot \beta \cdot I_s)\} * \{I_{in}/(M \cdot \beta \cdot I_s)\} * \{n \cdot \beta \cdot I_s / I_{ref}\} \\ &= VT \cdot \ln\{n \cdot I_{in}/(M \cdot N \cdot \beta \cdot I_s)\} \\ &= VT \cdot \ln\{I_{out}/(\beta \cdot I_s)\} \end{aligned} \quad (3)$$

Here, VT: thermal voltage

$\beta$ : current amplification factor

$I_s$ : saturation current

From the above equation (3), the following equation is found:

$$I_{out} = \{n/(M \cdot N)\} \cdot I_{in} \quad (4)$$

When  $n=1$ ,

$$I_{out} = \{1/(M \cdot N)\} \cdot I_{in} \quad (5)$$

That is, with respect to the input current  $I_{in}$ , the output current  $I_{out}$  is proportional to the reciprocal of the product (M·N) of the emitter areas of the two transistors of a multi-emitter configuration.

In order to obtain a very small output current  $I_{out}$ , it is only necessary to set the product (M·N) of the emitter area greater. For example, at  $M=5$  and  $N=5$  (corresponding to the pattern size of 10 transistors), it is possible to set  $1/(M \cdot N) = 1/25$ . In this connection, the M and N, exceeding 1, may be non-integer. If, for example,  $M=6.5$  and  $N=2$ , then a prime number, such as  $M \cdot N=13$ , can be set. Further, if  $M=6.5$  and  $N=3$ , then any arbitrary number, such as  $M \cdot N=19.5$ , can be set.

That is, according to the current source circuit shown in FIG. 3, by subtracting the base-to-emitter forward voltage  $V_{BEQ1}$  (a fixed value) of the transistor **Q1** from a sum of a small base-to-emitter forward voltage  $V_{BEQ2}$  of the transistor **Q2** of a multi-emitter configuration and small base-to-emitter forward voltage  $V_{BEQ3}$  of the transistor **Q3** of a multi-emitter configuration, the base-to-emitter forward voltage  $V_{BEQ4}$  of the transistor **Q4** for current outputting is suppressed to a lower extent and a very small output current  $I_{out}$  is obtained.

By doing so, it is possible to, being simpler in structure, suppress the pattern size of the transistors used and size of the IC chip and thereby to precisely obtain a very small output current.



FIG. 4 shows a circuit arrangement showing a current source circuit according to a second embodiment of the present embodiment.

The second embodiment is different from the first embodiment of FIG. 3 with respect to using a resistive element R in place of the input current source circuit 14. The remaining portion of FIG. 4 is the same as that of FIG. 3 and any further explanation is, therefore, emitted with the same reference numerals employed to designate parts or elements corresponding to those shown in FIG. 3.

In the current source circuit shown, the following equation is established.

$$\begin{aligned}
 VBEQ4 &= VBEQ2 + VBEQ3 - VBEQ1 \\
 VT \cdot 1n\{I_{ref}/(N \cdot \beta \cdot I_s)\} + VT \cdot 1n\{VBEQ2/(R \cdot M \cdot \beta \cdot I_s)\} - VT \cdot 1n\{I_{ref}/(n \cdot \beta \cdot I_s)\} \\
 &= VT \cdot 1n\{I_{ref}/(N \cdot \beta \cdot I_s)\} * \{VBEQ2/(R \cdot M \cdot \beta \cdot I_s)\} * \{n \cdot \beta \cdot I_s/I_{ref}\} \\
 &= VT \cdot 1n\{n \cdot VBEQ2/(R \cdot M \cdot N \cdot \beta \cdot I_s)\} \\
 &= VT \cdot 1n\{I_{out}/(\beta \cdot I_s)\} \\
 \therefore I_{out} &= n \cdot VBEQ2/(R \cdot M \cdot N)
 \end{aligned} \tag{6}$$

When  $n=1$ ,

$$I_{out} = VBEQ2/(R \cdot M \cdot N) \tag{7}$$

An output current  $I_{out}$  is proportional to the reciprocal of a value obtained by multiplying a resistive value of the resistive element by  $M \cdot N$ . In order to obtain a very small output current  $I_{out}$ , it is possible to minimize the pattern size of the resistive element R when, for example,  $N=5$  and  $M=5$ .

In this connection it is to be noted that another resistive element can be connected between the emitter of a first transistor Q1 and the collector of a second transistor Q2.

Since the current source circuits shown in FIGS. 3 and 4 are of such a type that those base-to-emitter circuits of NPN transistors Q3 and Q2 are connected, in a two-stage direct-connected configuration, between the power source node 11 and the GND to provide two base-to-emitter voltages VBE, a voltage of over  $2VBE$  (at least over 1.8V) is required as the operation power source. Therefore, the resultant power source circuit cannot be applied to an integrated circuit which is mounted on an electronic device capable of operating with a low power source voltage of a battery of, for example, below 1.5V.

With these situations in view, an explanation will be given below about a current source circuit operable under a low power source voltage of below 1.5V such as a voltage of about 0.9V.

FIG. 5 shows a circuit arrangement of a current source circuit according to a third embodiment of the present invention. The emitter-to-collector circuit of a first transistor Q1 of a PNP type having its collector and base connected together and collector-to-emitter circuit of a second transistor Q2 of an NPN type having a multi-emitter configuration are series-connected together between a power source node 11 and GND.

An emitter-to-collector circuit of a third transistor Q3 of a PNP type having its base connected to the base of the transistor Q1 and collector-to-emitter circuit of a fourth transistor of an NPN type having its collector and base connected together are series-connected together between the power source node 11 and the GND.

An input current source circuit 14 flowing an input current  $I_{in}$  therein and collector-to-emitter circuit of a fifth transistor Q5 of an NPN type connected at its base to the base of the

transistor Q4 and having a multi-emitter configuration are series-connected together across the power source node 11 and the GND.

Further, a collector-to-emitter circuit of a sixth transistor Q6 of an NPN type for current outputting is connected between a current output node 12 and the GND. The transistor Q6 is connected at its base to the base of the second transistor Q2 and collector of the transistor Q5.

In the case where the emitter area of the transistor Q6 is as a reference ( $=1$ ), the emitter area of the transistor Q2 is set to N-fold and that of the transistor Q5 is set to M-fold.

Under the application of the power source voltage  $V_{cc}$ , the input current  $I_{in}$  provides a base current of the transistor Q2 and the transistor Q1 to Q5 operate in the order of  $Q2 \rightarrow Q1 \rightarrow Q3 \rightarrow Q4 \rightarrow Q5$ .

When the base-to-emitter forward voltages of the transistors Q1 to Q5 are represented by  $VBEQ1$  to  $VBEQ5$ , the collector currents of the transistors Q1 to Q5 by  $ICQ1$  to  $ICQ5$  and the collector current (output current) of the transistor Q6 by  $I_{out}$ , then a current of  $I_{in} - ICQ5$  is supplied to the base of the transistor Q2 and the collector currents of the transistors Q1, Q3 and Q4 are increased. As a result, the collector current  $ICQ5$  in the transistor Q2 operates toward a base current decreasing direction.

In the case of  $I_{in} < ICQ5$ , on the other hand, the base current in the transistor Q2 is decreased by a current corresponding to  $ICQ5 - I_{in}$  and, therefore, the collector currents of the transistors Q1, Q3, Q4 are decreased. As a result, the collector current  $ICQ5$  of the transistor Q5 is decreased and the base current in the transistor Q2 operates toward a base current increasing direction.

That is, a negative feedback is applied to the base of the transistors Q2 via the transistors  $Q2 \rightarrow Q1 \rightarrow Q3 \rightarrow Q4 \rightarrow Q5$ , so that the operation of the circuit becomes stable in a state corresponding to substantially  $I_{in} = ICQ5$ .

Here, the collector current  $ICQ2$  of the transistor Q2, if its base current is disregarded for brevity in explanation, becomes

$$ICQ2 = ICQ1 = ICQ3 = ICQ4$$

Since  $ICQ5 = I_{in} = M \times ICQ4$ ,  
 $ICQ2 = I_{in}/M$ .

Since  $I_{out} = ICQ2/N$ ,

$$I_{out} = \{1/(M \cdot N)\} \cdot I_{in} \tag{8}$$

The output current  $I_{out}$  becomes a value obtained by multiplying the input current  $I_{in}$  by the reciprocal of a product ( $M \times N$ ) of the emitter area ratios ( $M \times N$ ) of the two transistors Q5 and Q2 of a multi-emitter configuration.

Further, since only a voltage of the base-to-emitter forward voltage VBE and the collector-to-emitter voltage VCE of the transistors (that is  $VBEQ1 + VCEQ2$  or  $VBEQ4 + VCEQ3$ ) is included between the power source node 11 and the GND, a low voltage operation is possible. If, for example,  $VBE = 0.7V$  and the collector-to-emitter saturation voltage  $V_{CESAT} = 0.2V$ , the minimal operation voltage becomes 0.9V and the operation is possible even if  $V_{cc}$  falls down to 0.9V.

FIG. 6 shows a circuit arrangement of a current source circuit according to a fourth embodiment of the present invention. The fourth embodiment is different from the current source circuit shown in FIG. 3 in that, between the emitter of the transistor Q3 and GND, the base-to-emitter circuits of those transistors Q3 and Q5 are connected in a two-stage direct-connected configuration to provide two base-to-emitter forward voltage (VBE) and, accordingly,

between the base of the transistor **Q3** and that of an output transistor **Q4**, the base-to-emitter circuits of two diode-connected transistors **Q1** and **Q6** are connected in a series-connected configuration. The fourth embodiment is the same as the circuit of FIG. 3 and, in FIG. 4, the same reference numerals are employed to designate parts or elements corresponding to those shown in FIG. 3 and any further explanation is, therefore, omitted.

That is, (1) the base-to-emitter circuit of a fifth transistor **Q5** of an NPN type having a multi-emitter configuration and is connected between the emitter of the transistor **Q3** and the base of a transistor **Q2**, (2) the base-to-emitter circuit of the diode-connected transistor **Q6** is inserted between the emitter of the diode-connected transistor **Q1** and the base of the output transistor **Q4** and (3) a current source circuit **15** flowing a bias current  $I_{in}$  is inserted between the emitter of the transistor **Q5** and GND.

If the emitter area ratio of the transistor **Q5** is represented by  $L$  when the emitter area of the output transistor **Q4** is taken as a reference ( $=1$ ), the base currents of the respective transistors are disregarded for brevity in explanation and  $\beta$ ,  $I_s$  of the respective transistors are equal, the following relation is established. The base potential  $V_{BEQ4}$  of the output transistor **Q4** becomes

$$\begin{aligned} V_{BEQ4} &= V_{BEQ2} + V_{BEQ5} + V_{BEQ3} - V_{BEQ1} - V_{BEQ6} \\ &= VT \cdot 1n \left[ \frac{I_{ref}}{\beta \cdot I_s} \cdot \frac{I_{ref}}{\beta \cdot I_s} \cdot \frac{I_{in}}{M \cdot \beta \cdot I_s} \cdot \frac{I_{ref}}{\beta \cdot I_s} \right] \\ &= VT \cdot 1n \left[ \frac{I_{in}}{L \cdot M \cdot N \cdot \beta \cdot I_s} \right] \\ &= VT \cdot 1n \left[ \frac{I_{out}}{\beta \cdot I_s} \right] \\ \therefore I_{out} &= \left( \frac{1}{L \cdot M \cdot N} \right) \cdot I_{in} \end{aligned} \quad (9)$$

That is, the output  $I_{out}$  is proportional to the reciprocal of a product ( $L \cdot M \cdot N$ ) of the emitter areas of the three transistors **Q5**, **Q3**, **Q2** of the multi-emitter configuration.

FIG. 7 shows a current source circuit according to a fifth embodiment of the present invention.

The fifth embodiment is different from the circuit of FIG. 6 in that, between the emitter of the transistor **Q3** and the GND in FIG. 6, those base-to-emitter circuits of  $n$  transistors are connected in an  $n$  (integer)-stage direct-circuit configuration to provide  $n$  base-to-emitter forward voltages  $V_{BE}$  and, accordingly, the base-to-emitter circuits of the  $n$  transistors are connected, in an  $n$ -stage direct-connected configuration, between the base of the transistor **Q3** and the base of the output transistor **Q4**.

That is, between the base of an NPN type transistor **QA1** of a multi-emitter configuration connected at its emitter to the GND and the emitter of an NPN type transistor **QAn** of a multi-emitter configuration connected at its collector to a power source node, the base-to-emitter circuits of  $n-2$  NPN type transistors **QA2** to **QAn-1** of a multi-emitter configuration are connected at an  $(n-2)$ -stage direct-connected configuration to provide a Darlington-connected configuration.

Current source circuits **512** to **51n-1** flowing bias currents  $I_{ref}$  are each connected between the corresponding emitter of the  $n-2$  transistors **QA2** to **QAn-1** and GND and an input current source circuit **14** for flowing an input current  $I_{in}$  is connected between the transistor **QAn** and the GND.

The base-to-emitter circuits of  $n-1$  transistors **Q1** to **Qn-1** and **Qn** are connected between the base of the transistor **QAn** and the GND to provide a corresponding-stage direct-circuit configuration, those transistors **Q1** to **Qn-1** being each connected as a diode connection and the transistor **Qn** serves as an output transistor.

Between the power source node **11** and the collector of the transistor **Q1** a reference current source circuit **13** is connected to provide a reference current  $I_{ref}$ .

If the emitter areas of the Darlington-connected transistors **QA1** to **QAn** are represented by  $N1$  to  $Nn$ , the emitter area ratio of the diode-connected transistors **Q1** to **Qn-1** by  $L1$  to  $Ln-1$  and the area ratio of the output transistor **Qn** by  $L_n$ , the base current of the respective transistors are disregarded for brevity in explanation and  $\beta$ ,  $I_s$  of the respective transistors are equal, then the following relation is established.

The base potential  $V_{BEQn}$  of the output transistor **Qn** becomes

$$\begin{aligned} V_{BEQn} &= V_{BEQA1} + V_{BEQA2} + \dots + V_{BEQAn-1} + V_{BEQAn} - V_{BEQ1} - V_{BEQ2} - \dots - V_{BEQn-1} \\ &= VT \cdot 1n \left[ \frac{I_{ref}}{\beta \cdot I_s} \cdot \frac{I_{ref}}{\beta \cdot I_s} \cdot \dots \cdot \frac{I_{ref}}{\beta \cdot I_s} \cdot \frac{I_{in}}{Nn \cdot \beta \cdot I_s} \cdot \frac{I_{ref}}{\beta \cdot I_s} \cdot \frac{I_{ref}}{\beta \cdot I_s} \cdot \dots \cdot \frac{I_{ref}}{\beta \cdot I_s} \right] \\ &= VT \cdot 1n \left[ \frac{I_{in}}{\beta \cdot I_s} \right] \\ &= VT \cdot 1n \left[ \frac{I_{out}}{L_n \cdot \beta \cdot I_s} \right] \end{aligned} \quad (11)$$

$$\therefore I_{out} = \left( \frac{1}{L1 \cdot L2 \cdot \dots \cdot Ln-1 \cdot Ln} \right) \cdot \frac{I_{in}}{N1 \cdot N2 \cdot \dots \cdot Nn-1 \cdot Nn} \quad (12)$$

That is, relative to the input current  $I_{in}$ , the output current  $I_{out}$  becomes proportional to a product ( $L1 \cdot L2 \cdot \dots \cdot Ln-1 \cdot Ln$ ) of the emitter ratios of the  $n-1$  transistors **Q1** to **Qn-1** and **Qn** and proportional to the reciprocal of a product ( $N1 \cdot N2 \cdot \dots \cdot Nn-1 \cdot Nn$ ) of the  $n$  transistors **QA1** to **QAn** of the multi-emitter configuration.

Here,  $L1=L2=L3=\dots=L_{n-1}=L_n=1$ . Then

$$I_{out} = \left( \frac{1}{N1 \cdot N2 \cdot \dots \cdot N_{n-1} \cdot Nn} \right) \cdot I_{in} \quad (13)$$

That is, relative to the input current  $I_{in}$ , the output current  $I_{out}$  becomes proportional to the reciprocal of a product ( $N1 \cdot N2 \cdot \dots \cdot N_{n-1} \cdot Nn$ ) of the emitter area ratios of the  $n$  transistors **QA1** to **QAn** of the multi-emitter configuration.

FIG. 8 shows a current source circuit according to a sixth embodiment of the present invention.

The sixth embodiment is different from the current source circuit of FIG. 7 in that, with the emitter area ratios of respective transistors represented as 1, current source circuits **612** to **61n-1** are so connected to the emitters of those transistors **QA2** to **QAn-1** of  $n$  transistors **QA1** to **QAn** of a Darlington connection as to be given corresponding weighted currents  $I_{ref}/A2$  to  $I_{ref}/An-1$ . The remaining portion of the circuit of FIG. 8 is the same as that of FIG. 7 and any further explanation is omitted with the same reference numerals used to designate parts or elements corresponding to those shown in FIG. 7.

If, for brevity in explanation, the base current of the respective current is disregarded and  $\beta$ ,  $I_s$  of the respective transistors are equal, then the following relation is established.

The base potential  $V_{BEQn}$  of the output transistor **Qn** becomes

$$\begin{aligned} V_{BEQn} &= V_{BEQA1} + V_{BEQA2} + \dots + V_{BEQAn-1} + V_{BEQAn} - V_{BEQ1} - V_{BEQ2} - \dots - V_{BEQn-1} \\ &= VT \cdot 1n \left[ \frac{I_{ref}}{\beta \cdot I_s} \cdot \frac{I_{ref}}{\beta \cdot I_s} \cdot \dots \cdot \frac{I_{ref}}{\beta \cdot I_s} \cdot \frac{I_{in}}{\beta \cdot I_s} \cdot \frac{I_{ref}}{\beta \cdot I_s} \cdot \frac{I_{ref}}{\beta \cdot I_s} \cdot \dots \cdot \frac{I_{ref}}{\beta \cdot I_s} \right] \\ &= VT \cdot 1n \left[ \frac{I_{in}}{\beta \cdot I_s} \right] \\ &= VT \cdot 1n \left[ \frac{I_{out}}{\beta \cdot I_s} \right] \end{aligned} \quad (14)$$

$$\therefore I_{out} = \left( \frac{1}{A2 \cdot \dots \cdot An-1} \right) \cdot I_{in} \quad (15)$$

Relative to an input current  $I_{in}$ , the output current  $I_{out}$  is proportional to the reciprocal of a product  $(A2 \cdot A3 \cdot \dots \cdot An-1)$  of the current source circuits 612 . . . 61n-1. Here, if  $(A2 \cdot A3 \cdot \dots \cdot An-1) > 1$  is given, the output current  $I_{out}$  smaller than the input current  $I_{in}$  is obtained. If, however,  $(A2 \cdot A3 \cdot \dots \cdot An-1) < 1$  is given, the output current  $I_{out}$  greater than the input current  $I_{in}$  is obtained.

FIG. 9 shows a current source circuit according to the seventh embodiment of the present embodiment.

A practical form of a circuit is of such a type that resistive elements R2, R3, . . . Rn-1 are used to produce the reference current  $I_{ref}$  in the reference current source circuit 13 and the weighted currents  $I_{ref}/A2$  . . .  $I_{ref}/An-1$  in the current source circuits 612 . . . 61n-1 connected to the emitters of the transistors QA2 . . . QAn-1 of the n transistors QA1 . . . QAn of the Darlington connection. Here, the same reference numerals are employed to designate parts or elements corresponding to those in FIG. 8 and any further explanation is omitted.

A first resistive element R01, the emitter-to-collector circuit of a PNP transistor Q701 having its base and collector connected to each other and reference current source 13 flowing a reference current  $I_{ref}$  are connected, in a series array, between a power source node 11 and GND.

A second resistive element R02 and emitter-to-collector circuit of a PNP transistor Q702 are series-connected between the power source node 11 and the collector of the diode-connected transistor Q1.

A third resistive element R03, emitter-to-collector circuit of a PNP transistor Q703, collector-to-emitter circuit of an NPN transistor Q704 having its collector and base connected together and a fourth resistive element R04 are series-connected between the power source node 11 and the GND.

The PNP transistors Q701, Q702 and Q703 have their bases connected together to provide a first current mirror circuit.

Between the respective emitter of the transistors QA2 . . . QAn-1 of the n transistors QA1 to QAn of a Darlington connection and the GND, a corresponding current source is connected. Those respective current source circuits are comprised of the collector-to-emitter paths of series-connected NPN transistors Q712 to Q71n-1 and resistive elements R2 to Rn-1.

The NPN transistors Q712 to Q71n-1 and Q704 have their bases connected together to provide a second current mirror circuit.

Assuming  $R_{01}=R_{02}=R_{03}=R_{04}=R_0$  in FIG. 9, those resistive ratios  $(R2/R0)$ ,  $(R3/R0)$  . . . ,  $(Rn-1/R0)$  in FIG. 9 correspond to the weighted coefficients A2, . . . , An-1 of those current source circuits 612 . . . 61n-1 in FIG. 8 and hence

$$I_{out}=(R0^{n-2}/R2 \cdot \dots \cdot Rn-1) \cdot I_{in} \quad (16)$$

That is, relative to the input current  $I_{in}$ , the output current  $I_{out}$  is proportional to the (n-2)nd power of the resistive value of the resistive element R0 and proportional to the reciprocal of a product of the weighted coefficients of those resistive elements R2-R3 . . . Rn-1.

If  $(R2 \cdot \dots \cdot Rn-1) > R0^{n-2}$ , then an output current  $I_{out}$  smaller than  $I_{in}$  is obtained, while, on the other hand, if  $(R2 \cdot \dots \cdot Rn-1) < R0^{n-2}$ , the output current  $I_{out}$  greater than the input current  $I_{in}$  is obtained.

Additional advantages and modifications will readily occur to those skilled in the art. Therefore, the invention in its broader aspects is not limited to the specific details and representative embodiments shown and described herein.

Accordingly, various modifications may be made without departing from the spirit or scope of the general inventive concept as defined by the appended claims and their equivalents.

What is claimed is:

1. A current source circuit comprising:

a series-circuit connected between a power supply node and ground comprising,

a reference current source circuit,

a first transistor having an NPN configuration and having its collector and base connected to each other and

a second transistor having an emitter area N-fold a reference area, wherein N is greater than 1;

a third transistor having an NPN configuration and connected to the power supply node at its collector, connected to the base of the first transistor connected to the base of the second transistor at its emitter, and having an emitter area M-fold the reference area, wherein M is greater than 1;

an input current source circuit connected between the emitter of the third transistor and the ground to provide an input current; and

a fourth transistor having an NPN configuration and having an emitter area equal to the reference area and having its collector-to-emitter circuit connected between a current output node and the ground and its base connected to the collector of the second transistor in order to provide an output current, wherein

the output current relative to the input current is proportional to a reciprocal of a product  $M \times N$  of the emitter areas of the second and third transistors.

2. The current source circuit according to claim 1, wherein the emitter area of the fourth transistor is one and an emitter area of the first transistor is n-fold the reference area.

3. The current source circuit according to claim 2, wherein the emitter area of the first transistor is n-1-fold the reference area.

4. The current source circuit according to claim 1, wherein the input current source circuit comprises a resistor.

5. A current source circuit comprising:

a first group of n-1 transistors (Q1, Q2, . . . , Qn-1) of an NPN type having one end connected to an other end of a reference current source circuit having one end connected to a power source node, having their collector and base connected to each other, having their emitter area ratios L1 . . . Ln-1 and each having a multi-emitter configuration, these transistors being series-connected together and each providing a diode connection;

an output transistor Qn of a multi-emitter configuration having its collector-to-emitter circuit connected between a current output node and a ground and its base connected to the emitter of the transistor Qn-1 at the other end of the first transistor group and having an emitter area ratio Ln, the output transistor Qn providing an output current  $I_{out}$ ;

a second group of transistors (QA1, QA2, . . . , QAn) comprising a first transistor QA1 of an NPN type having its collector-to-emitter circuit connected between the emitter of the transistor Qn-1 at the other end of the first group of transistors and ground and having a multi-emitter configuration, an n-th transistor QAn of an NPN type having its collector connected to the power source node and its base connected to the base of one transistor of the first transistor group and having a multi-emitter configuration, and n-2 transis-

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tors of an NPN type having a multi-emitter configuration and Darlington-connected between the base of the first transistor **QA1** and the emitter of the n-th transistor **QAn** said second group of transistors (**QA1**, **QA2**, . . . **QAn**) having their emitter area **N1**, **N2**, . . . **Nn**, wherein the collector-to-emitter circuits of the second to (n-1)-st transistors (**QA2**, . . . , **QAn-1**) of the second transistor group are connected between the power source node and the ground;

an input current source circuits connected between the emitter of the n-th transistor **QAn** and the ground to provide an input current **Iin**; and

n-2 bias current source circuits connected between the corresponding emitters of the second to the n-1 transistors (**QA2**, . . . , **QAn-1**) of the second transistors group and the ground, wherein, relative to the input current **Iin**, the output current **Iout** is proportional to a product (**L1**·**L2**·. . . ·**Ln**) of those emitter area ratios of those diode-connected n-1 transistors **Q1** to **Qn-1** and output transistor **Qn** and proportional to the reciprocal of a product (**N1**·**N2**·. . . ·**Nn-1**·**Nn**) of the emitter area ratios of the second transistor group (**QA1**, **QA2**, . . . , **QAn**) where n represents an integer of over 2.

6. A current source circuit comprising:

a reference current source circuit having one end connected to a power source node;

a first group of n-1 transistors (**Q1**, **Q2**, . . . , **Qn-1**) of an NPN type having one end connected to the other end of the reference current source circuit, each having its collector and base connected to each other, and series-connected together as a diode connection each;

an output transistor **Qn** connected between a current output node and ground and connected at its base connected to the emitter of the transistor **Qn-1** at the other end of the first transistor group to provide an output current **Iout**;

a second group of transistors (**QA1**, **QA2**, . . . , **QAn**) comprising a first transistor **QA1** of an NPN type

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having a collector-to-emitter circuit connected between the emitter of the transistor **Qn-1** at the other end of the first transistor group and ground, an n-th transistor **QAn** of an NPN type connected at its collector to the power source node and at its base connected to the base of one transistor of the first transistor group, and n-2 transistors of an NPN type Darlington-connected between the base of the first transistor **QA1** and the emitter of the n-th transistor **QAn**, wherein the collector-to-emitter circuits of the second to the (n-1)-st transistors (**QA2**, . . . , **QAn-1**) of the second transistor group are connected between the power source node and the ground;

n-2 bias current source circuits connected between the corresponding emitters of the second to (n-1)-st transistors (**QA2**, . . . , **QAn-1**) of the second transistor group and the ground to provide those corresponding weighted currents (**Iref/A2**, **Iref/A3**, . . . , **Iref/An-1** where **A2**, **A3**, . . . , **An-1** represent the weighted factors); and

an input current source circuit connected between the emitter of the n-th transistor **QAn** and the ground to provide an input current **Iin**, wherein

the output current **Iout** is proportional to the reciprocal of a product (**A2**·**A3**·. . . ·**An-1**) of the weighted factors given to the n-2 bias current source circuits for allowing a flow of the corresponding weighted currents (**Iref/A2**, **Iref/A3**, . . . , **Iref/An-1**) relative to the input current **Iout**.

7. The current source circuit according to claim 6, wherein the n-2 bias current source circuits include resistive elements of those levels of currents of the corresponding weighted factors in the bias current source circuits.

8. The current source circuit according to claim 1, wherein said second and third transistors have multi-emitter configurations.

\* \* \* \* \*